

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	81512	((lower or bottom) near2 electrode\$3)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:15
2	BRS	L2	33372	(insulat\$6 or ILD) near8 (SiN or "silicon nitride" or PSG or "phospho silicate glass" or phospho-silicate or phosphosilicate)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:15
3	BRS	L3	466003 7	open\$6 or gap\$3 or trench\$6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:16
4	BRS	L4	466	(insulat\$6 or ILD) near8 (SiN or "silicon nitride") near8 (PSG or "phospho silicate glass" or phospho-silicate or phosphosilicate)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:16
5	BRS	L5	11243	damascene	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:16

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	68521	MOSFET or "metal oxide semiconductor field effect transistor"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:16
7	BRS	L7	364	((insulat\$6 or ILD) near8 (SiN or "silicon nitride" or PSG or "phospho silicate glass" or phospho-silicate or phosphosilicate)) same damascene	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:16
8	BRS	L8	95619	(up or top or upper) near2 electrode\$3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:16
9	BRS	L9	148	((lower or bottom) near2 electrode\$3)) same ((up or top or upper) near2 electrode\$3) same damascene	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:16
10	BRS	L10	429	bond\$6 adj pad adj electrode\$4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:16

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L11	56343	lift-off or (lift near2 off) or (lifted near2 off) or (lifting near2 off)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:16
12	BRS	L12	16	(bond\$6 adj pad adj electrode\$4) and (lift-off or (lift near2 off) or (lifted near2 off) or (lifting near2 off))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:17
13	IS&R	L27	933	(257/779).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:17
14	BRS	L13	25	"source pad electrode"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:17
15	BRS	L14	285	((lower or bottom) near2 electrode\$3)) same ((insulat\$6 or ILD) near8 (SiN or "silicon nitride" or PSG or "phospho silicate glass" or phospho-silicate or phosphosilicate)) same (open\$6 or gap\$3 or trench\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:17

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L15	7	((lower or bottom) near2 electrode\$3)) same ((insulat\$6 or ILD) near8 (SiN or "silicon nitride") near8 (PSG or "phospho silicate glass" or phospho-silicate or phosphosilicate))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:17
17	BRS	L16	36	((insulat\$6 or ILD) near8 (SiN or "silicon nitride") near8 (PSG or "phospho silicate glass" or phospho-silicate or phosphosilicate)) and damascene	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:17
18	BRS	L17	18	TiNiAg	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:17
19	BRS	L18	34	((insulat\$6 or ILD) near8 (SiN or "silicon nitride" or PSG or "phospho silicate glass" or phospho-silicate or phosphosilicate)) same damascene) and (MOSFET or "metal oxide semiconductor field effect transistor")	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:17
20	BRS	L19	36	((insulat\$6 or ILD) near8 (SiN or "silicon nitride") near8 (PSG or "phospho silicate glass" or phospho-silicate or phosphosilicate)) and damascene	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:17

	Type	L #	Hits	Search Text	DBs	Time Stamp
21	BRS	L20	29	((((lower or bottom) near2 electrode\$3)) same ((up or top or upper) near2 electrode\$3) same damascene) and @ad<20001226	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:17
22	BRS	L28	18	TiNiAg	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:18
23	IS&R	L29	2238	(438/612).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:23
24	IS&R	L31	213	(438/615).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 18:53
25	IS&R	L32	934	(257/762).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 19:17

	Type	L #	Hits	Search Text	DBs	Time Stamp
26	IS&R	L33	1257	(257/763).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 19:33
27	IS&R	L34	631	(257/766).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 19:41
28	IS&R	L35	415	(257/772).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/08/30 20:07